

Applications

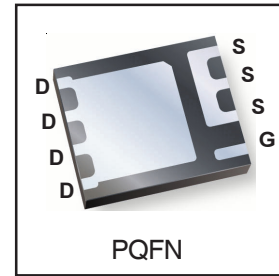
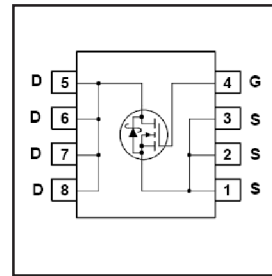
- Synchronous MOSFET for Notebook Processor Power
- Synchronous Rectifier MOSFET for Isolated DC-DC Converters in Networking Systems

HEXFET® Power MOSFET

V_{DS}	$R_{DS(on)}$ max	Qg
30V	3.3mΩ @ $V_{GS} = 10V$	34nC

Benefits

- Very low $R_{DS(on)}$ at 4.5V V_{GS}
- Low Gate Charge
- Fully Characterized Avalanche Voltage and Current
- 100% Tested for R_g
- Lead-Free (Qualified up to 260°C Reflow)
- RoHS compliant (Halogen Free)
- Low Thermal Resistance
- Large Source Lead for more reliable Soldering



Orderable part number	Package Type	Standard Pack		Note
		Form	Quantity	
IRFH7932TRPbF	PQFN 5mm x 6mm	Tape and Reel	4000	
IRFH7932TR2PbF	PQFN 5mm x 6mm	Tape and Reel	400	EOL notice # 259

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	
I_D @ $T_A = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	25	A
I_D @ $T_A = 70^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	20	
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	104	
I_{DM}	Pulsed Drain Current ①	200	
P_D @ $T_A = 25^\circ\text{C}$	Power Dissipation ②	3.4	W
P_D @ $T_A = 70^\circ\text{C}$	Power Dissipation ②	2.2	
	Linear Derating Factor ③	0.03	W/°C
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	2.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient ⑤	—	37	

Notes ① through ⑤ are on page 10

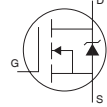
Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

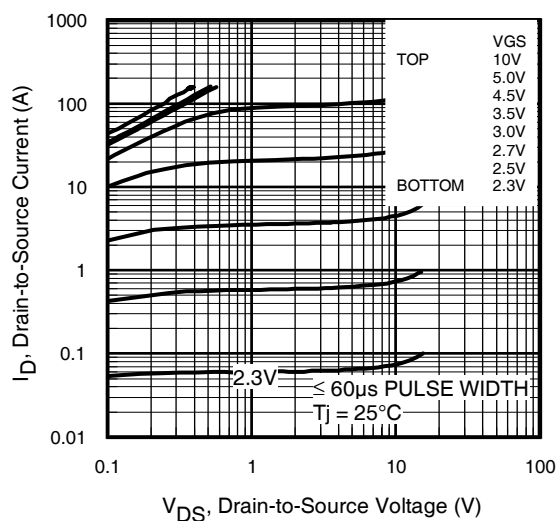
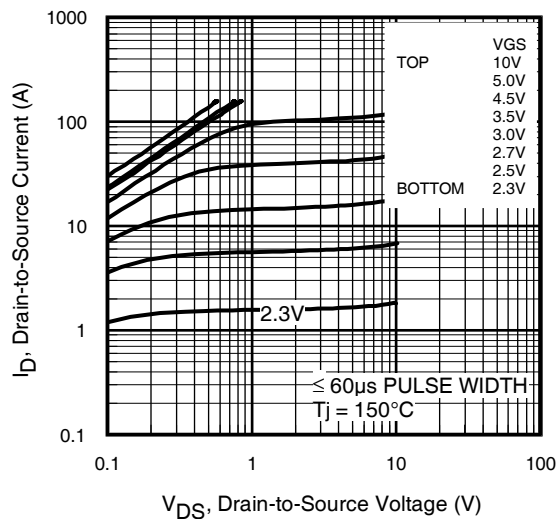
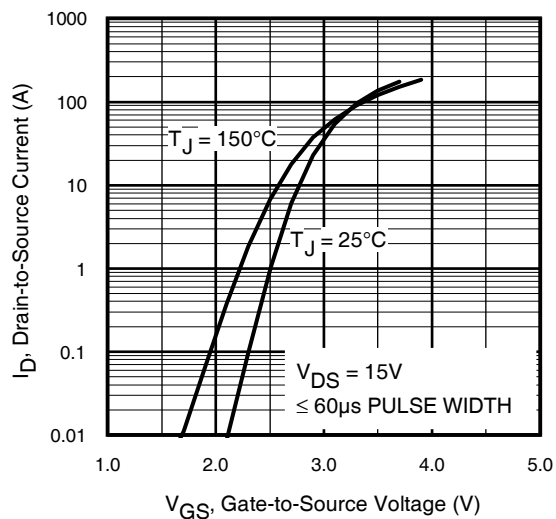
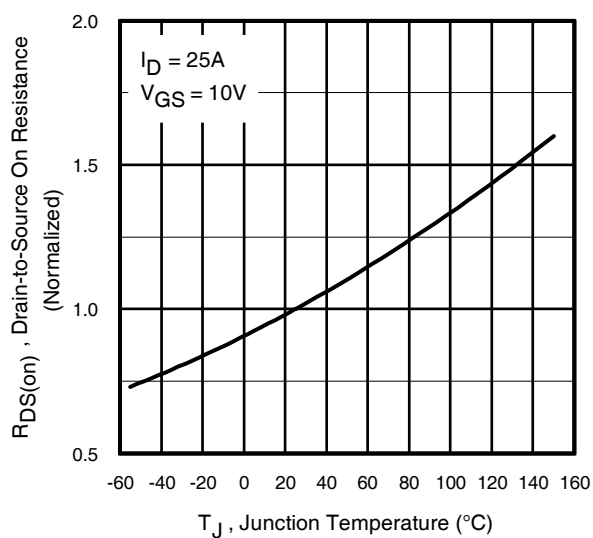
	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.021	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	2.5	3.3	$m\Omega$	$V_{GS} = 10V, I_D = 25A$ ③
		—	3.3	3.9		$V_{GS} = 4.5V, I_D = 20A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	1.35	1.8	2.35	V	$V_{DS} = V_{GS}, I_D = 100\mu A$
$\Delta V_{GS(th)}$	Gate Threshold Voltage Coefficient	—	-5.9	—	mV/ $^\circ\text{C}$	
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	150		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	59	—	—	S	$V_{DS} = 15V, I_D = 20A$
Q_g	Total Gate Charge	—	34	51	nC	$V_{DS} = 15V$ $V_{GS} = 4.5V$ $I_D = 20A$ See Fig.17 & 18
Q_{gs1}	Pre-V _{th} Gate-to-Source Charge	—	7.9	—		
Q_{gs2}	Post-V _{th} Gate-to-Source Charge	—	3.6	—		
Q_{gd}	Gate-to-Drain Charge	—	11	—		
Q_{godr}	Gate Charge Overdrive	—	12	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	15	—		
Q_{oss}	Output Charge	—	19	—	nC	$V_{DS} = 16V, V_{GS} = 0V$
R_G	Gate Resistance	—	0.7	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	20	—	ns	$V_{DD} = 15V, V_{GS} = 4.5V$ $I_D = 20A$ $R_G = 1.8\Omega$ See Fig.15
t_r	Rise Time	—	48	—		
$t_{d(off)}$	Turn-Off Delay Time	—	23	—		
t_f	Fall Time	—	20	—		
C_{iss}	Input Capacitance	—	4270	—	pF	$V_{GS} = 0V$ $V_{DS} = 15V$ $f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	830	—		
C_{rss}	Reverse Transfer Capacitance	—	420	—		

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	16	mJ
I_{AR}	Avalanche Current ①	—	20	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	4.2	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	200		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	$T_J = 25^\circ\text{C}, I_S = 20A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	21	32	ns	$T_J = 25^\circ\text{C}, I_F = 20A, V_{DD} = 15V$
Q_{rr}	Reverse Recovery Charge	—	33	50	nC	$di/dt = 300A/\mu s$ ③ See Fig.16
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

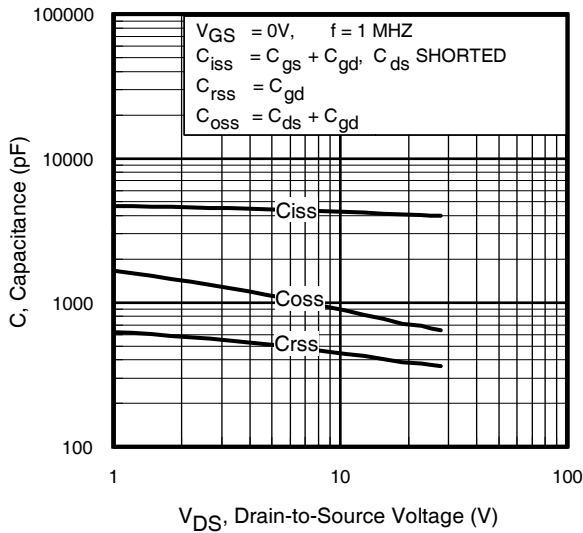


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

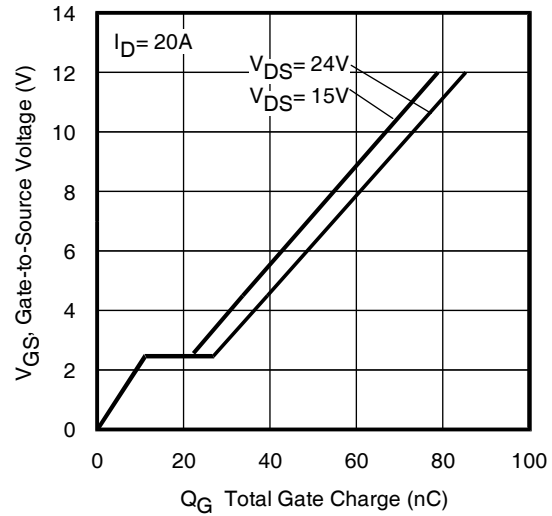


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

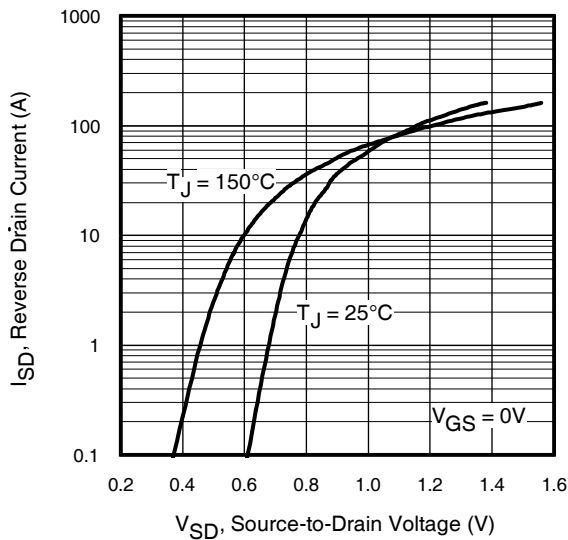


Fig 7. Typical Source-Drain Diode Forward Voltage

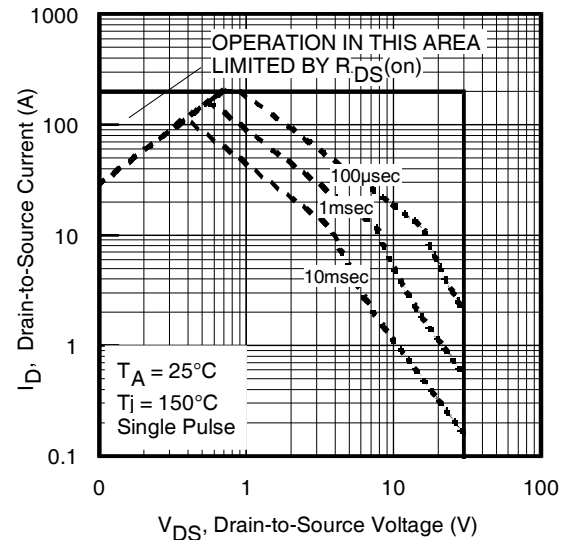


Fig 8. Maximum Safe Operating Area

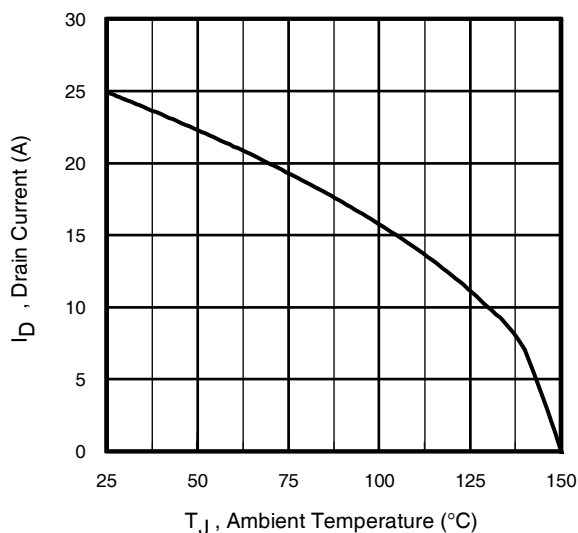


Fig 9. Maximum Drain Current Vs. Ambient Temperature

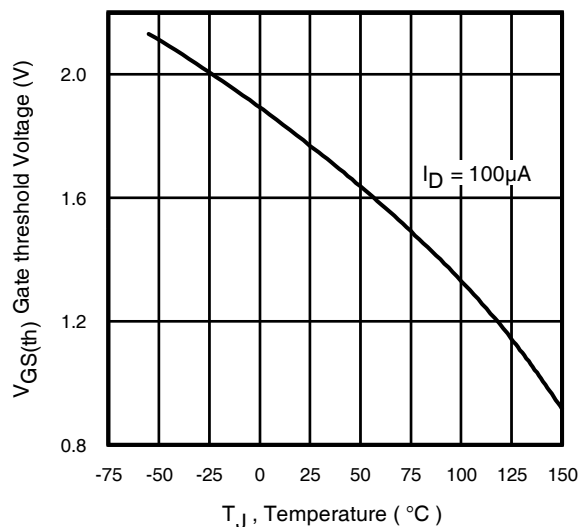


Fig 10. Threshold Voltage Vs. Temperature

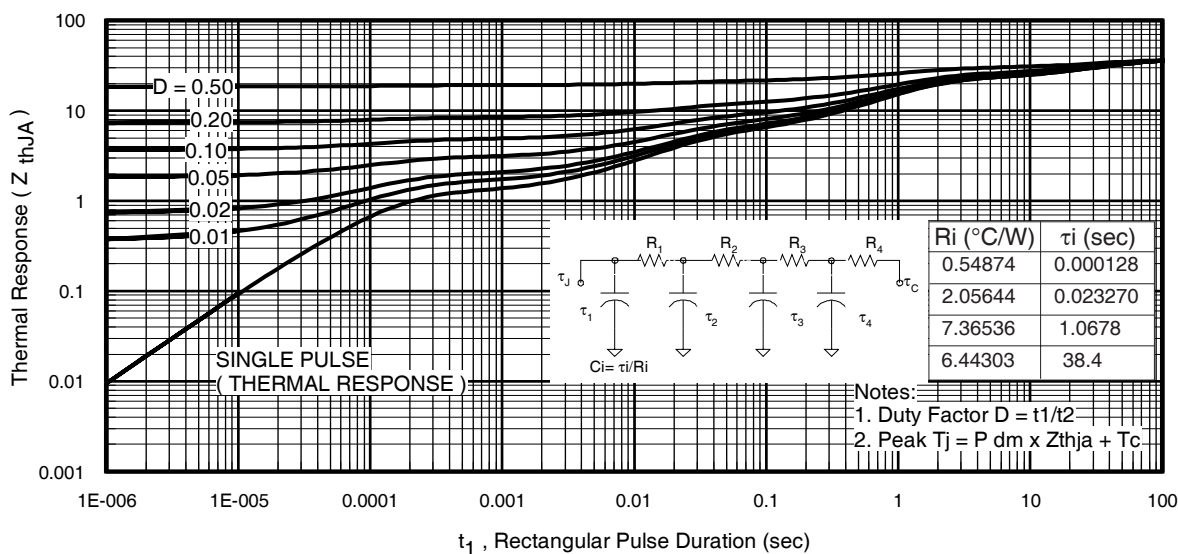
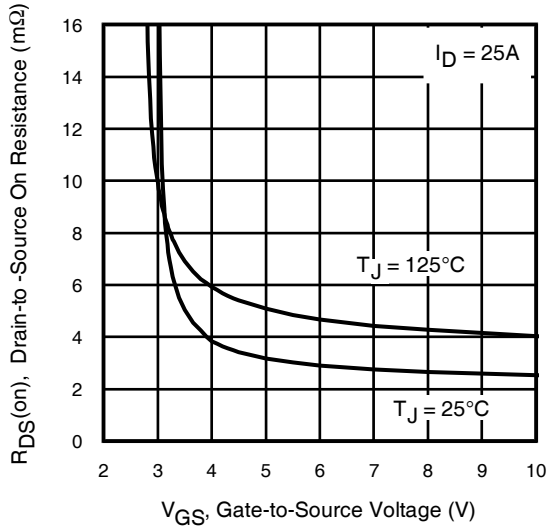
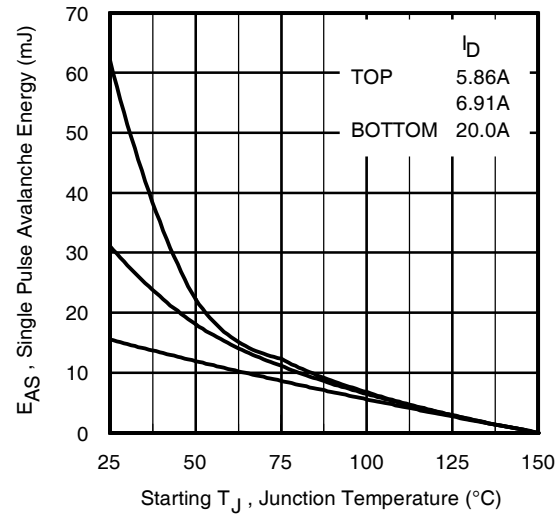
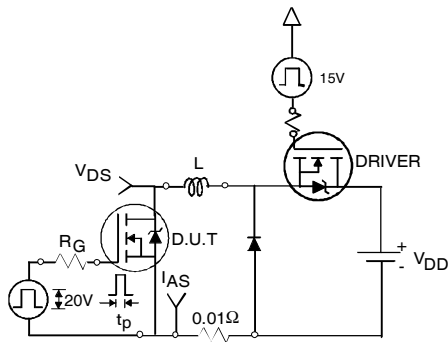
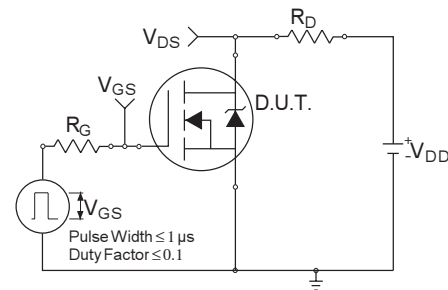
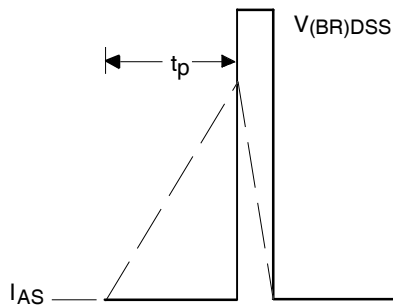
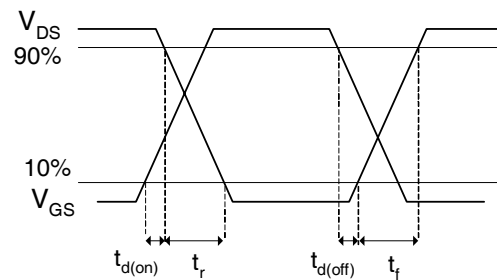


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Fig 12. On-Resistance vs. Gate Voltage

Fig 13. Maximum Avalanche Energy vs. Drain Current

Fig 14a. Unclamped Inductive Test Circuit

Fig 15a. Switching Time Test Circuit

Fig 14b. Unclamped Inductive Waveforms

Fig 15b. Switching Time Waveforms

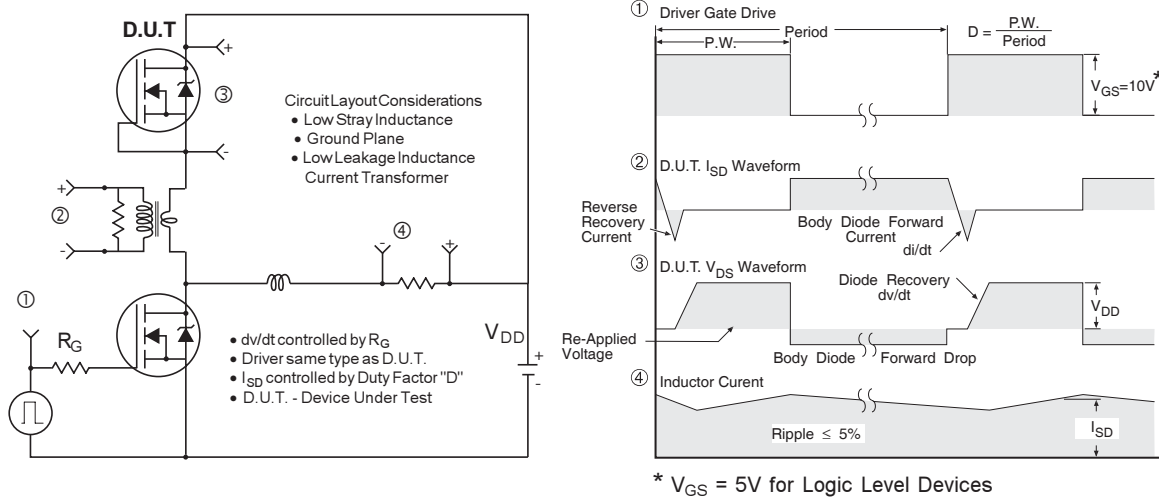


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

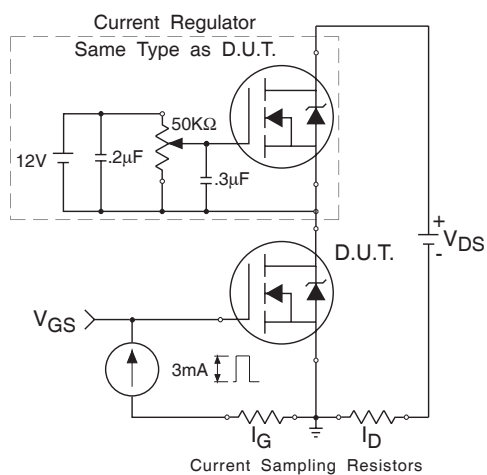


Fig 17. Gate Charge Test Circuit

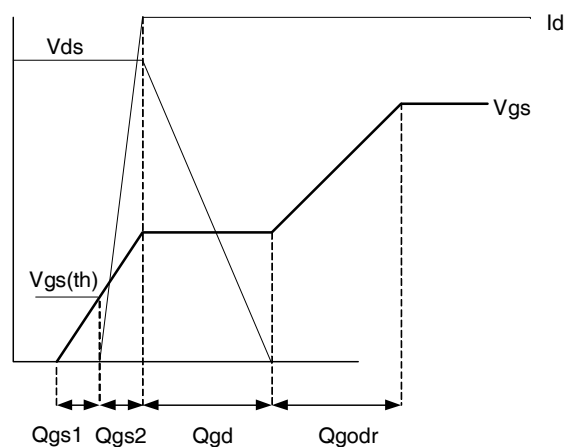
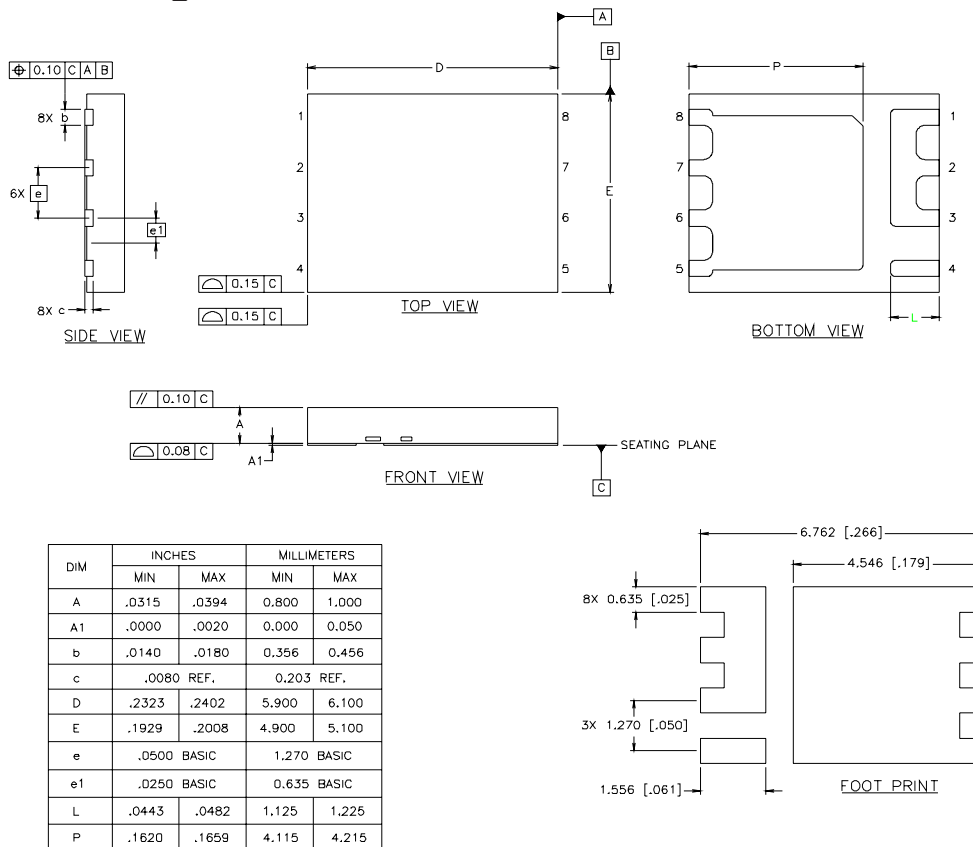
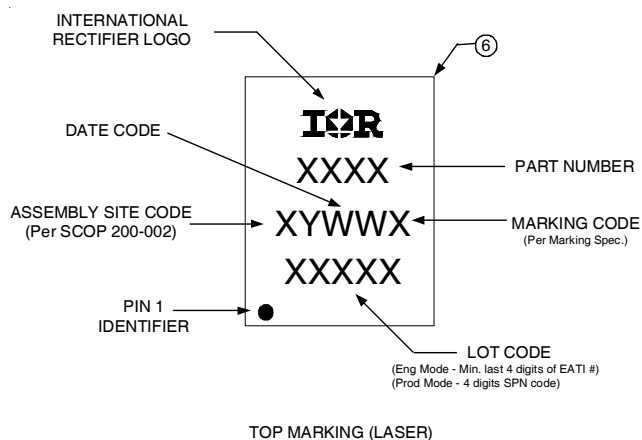


Fig 18. Gate Charge Waveform

PQFN Package Details

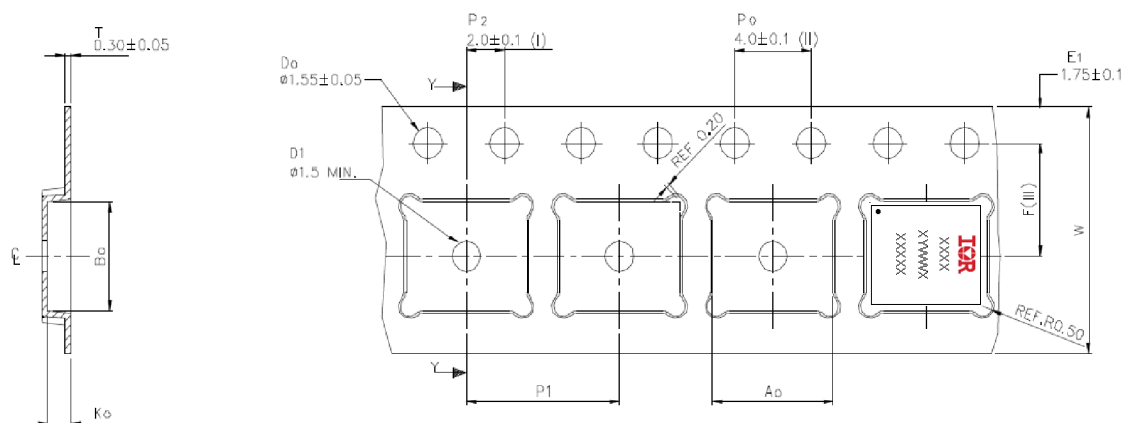


PQFN Part Marking



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

PQFN Tape and Reel



SECTION Y-Y

A_0	6.30 ± 0.1
B_0	5.30 ± 0.1
K_0	1.20 ± 0.1
F	5.50 ± 0.1
P_1	8.00 ± 0.1
W	12.00 ± 0.3

- (I) Measured from centreline of sprocket hole to centreline of pocket.
- (II) Cumulative tolerance of 10 sprocket holes is ± 0.20 .
- (III) Measured from centreline of sprocket hole to centreline of pocket.
- (IV) Other material available.
- (V) Typical SR of form tape Max 10^9 OHM/SQ

ALL DIMENSIONS IN MILLIMETRES UNLESS OTHERWISE STATED.

Qualification Information[†]

Qualification level	Consumer ^{††} (per JEDEC JESD47F ^{†††} guidelines)	
Moisture Sensitivity Level	SO-8	MSL1 (per JEDEC J-STD-020D ^{†††})
RoHS Compliant	Yes	

[†] Qualification standards can be found at International Rectifier's web site

<http://www.irf.com/product-info/reliability>

^{††} Higher qualification ratings may be available should the user have such requirements.
Please contact your International Rectifier sales representative for further information:

<http://www.irf.com/whoto-call/salesrep/>

^{†††} Applicable version of JEDEC standard at the time of product release.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^{\circ}\text{C}$, $L = 0.078\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 20\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ Rthjc is guaranteed by design
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.

Revision History

Date	Comments
12/16/2013	• Updated ordering information to reflect the End-Of-life (EOL) of the mini-reel option (EOL notice #259) • Updated data sheet with new IR corporate template
8/1/2014	• Updated data sheet with PQFN Tape and Reel Diagram from Datasheet IRFH7934PbF

International
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To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>